

/ Descriptions

TR0459 M M QSQ æ M ç s ll 1 Silicon NPN transistor in a TO-126 Plastic Package.

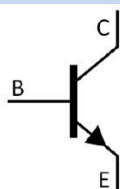
/ Features

I ð S_F=418W ε Ta=58 † ζ
High Power Dissipation :P_C=1.5W(Ta=25).

/ Applications

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Low collector saturation voltage ,large current.

/ Equivalent Circuit



/ Pinning



PIN1 χ Emitter PIN 2 χ Collector PIN 3 χ Base

/ h_{FE} Classifications & Marking

M 1 " See Marking Instructions.

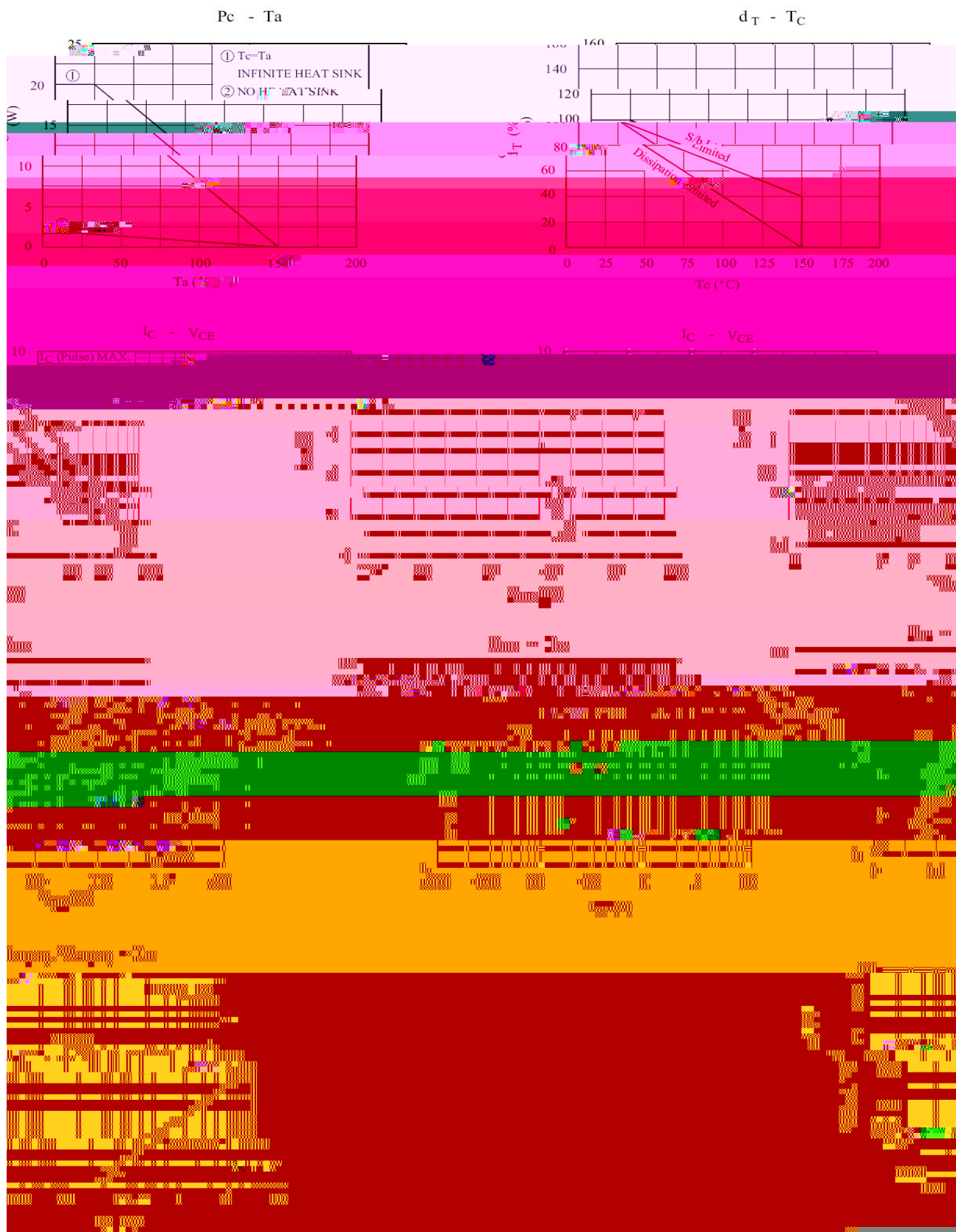
/ Absolute Maximum Ratings(Ta=25 °C)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	60	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current - Continuous	I_C	5.0	A
Peak Collector Current	I_{CP}	8.0	A
Base Current - Continuous	I_B	1.0	A
Collector Power Dissipation	P_C	1.5	W
Collector Power Dissipation	$P_C(T_c=25^\circ C)$	20	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

/ Electrical Characteristics(Ta=25 °C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-off Current	I_{CBO}	$V_{CB}=50V$ $I_E=0$			10	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=7V$ $I_C=0$			10	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=1.0V$ $I_C=2.0A$	100		400	
	$h_{FE(2)}$	$V_{CE}=1.0V$ $I_C=0.1A$	60			
	$h_{FE(3)}$	$V_{CE}=2.0V$ $I_C=5.0A$	50			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2.0A$ $I_B=0.2A$		0.1	0.3	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=2.0A$ $I_B=0.2A$		0.9	1.2	V
Turn On Time	t_{on}	$V_{CC}=10V$ $I_B=0.2A$		0.2	1	μs
Fall Time	t_f			1.1	2.5	μs
Storage Time	t_s			0.2	1	μs

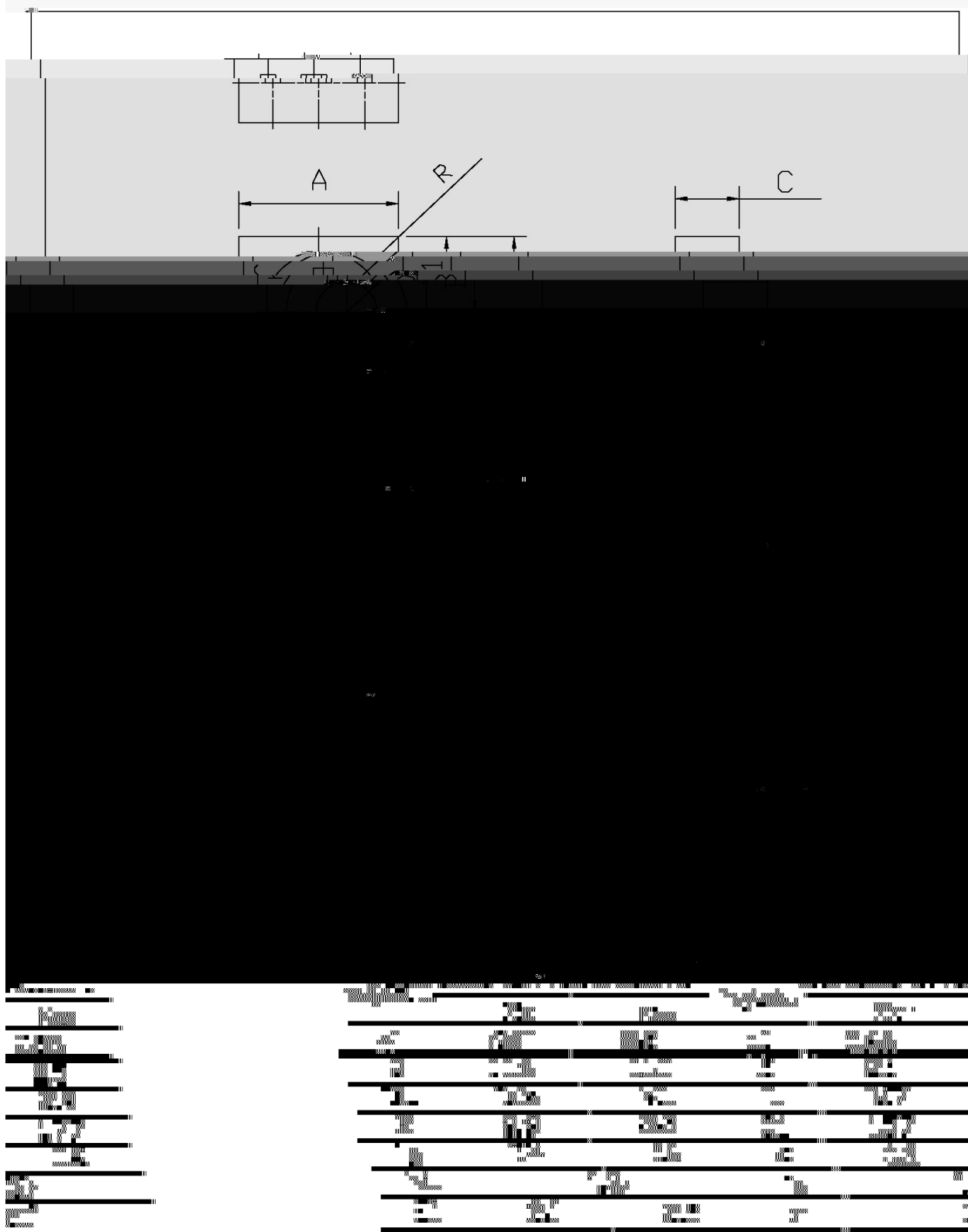
/ Electrical Characteristic Curve



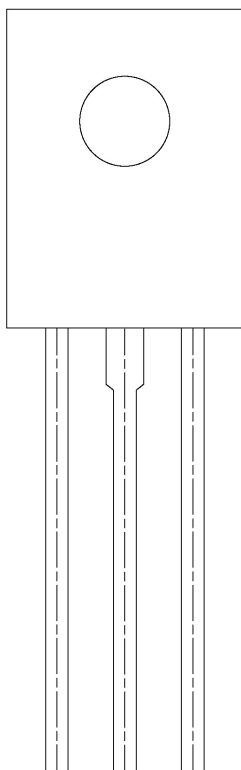
/ Package Dimensions

TQ-126

单位: mm



/ Marking Instructions



”	χ	
ER	χ	ᄃ 3 ^N ᄃ
G4994	χ	ᄃ 3 ^N ᄃ
****	χ	ᄃ 1 ㅍ ᄃ ^N ᄃ 1 1 ㅍ ᄃ ^N ㅍ ᄃ
Note:		
BR:		

$$ER \chi$$

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G4994 χ

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$$\mathbb{H} \cdot \mathbb{F} \check{\eta}^N \Gamma_D \quad \quad \quad \mathbb{I} \quad \quad \quad \mathbb{I} \cdot \mathbb{F} \check{\eta}^N \Psi \rho$$

Note:

BR:

() / Temperature Profile for Dip Soldering(Pb-Free)



1. Preheating: 25~150 °C, Time: 60~90sec;
2. Peak Temp.: 255 °C, Duration: 5~10sec;
3. Cooling Speed: 2~10 °C/sec.

- Note:
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/ Resistance to Soldering Heat Test Conditions

Temp.: 270 ± 5 °C, Time: 10 ± 1 sec.

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension (unit mm ³)		
	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Tube	Inner Box	Outer Box
TO-126/F	500	6	3,000	5	15,000	135×190	237×172×102	560×245×195

/ TUBE

Package Type	Units					Dimension (unit mm ³)		
	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Tube	Inner Box	Outer Box
TO-126/F	65	26	1,690	5	8,450	532×31×5.6	555×164×50	575×290×180

/ Notices